

October 1989 Revised August 1999

74FR16245

16-Bit Transceiver with 3-STATE Outputs

General Description

The 74FR16245 contains sixteen non-inverting bidirectional buffers with 3-STATE outputs and is intended for busoriented applications. Current sinking capability is 64 mA on both the A and B Ports. The device is byte controlled. Each byte has separate control inputs which can be shorted together for full 16-bit operation. The transmit/receive (T/\overline{R}_n) inputs determine the direction of data flow through the transceiver. The output enable (\overline{OE}_n) inputs disable both A and B Ports by placing them in an high impedance state.

Features

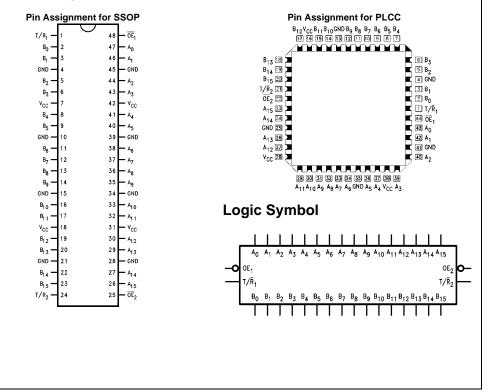
- Non-inverting buffers
- Bidirectional data paths
- A and B output sink capability of 64 mA, source capability of 15 mA
- Separate control pins for each byte
- Guaranteed pin-to-pin skew
- Low 3-STATE I_{II}
- 16-Bit version of the 74F245 or 74F645

Ordering Code:

Order Number	Package Number	Package Description
74FR16245QC	V44A	44-Lead Plastic Lead Chip Carrier (PLCC), JEDEC MO-047, 0.650 Square
74FR16245SSC	MS48A	48-Lead Small Shrink Outline Package (SSOP), JEDEC MO-118, 0.300 Wide

Devices also available in Tape and Reel. Specify by appending the suffix letter "X" to the ordering code.

Connection Diagrams



Pin Descriptions

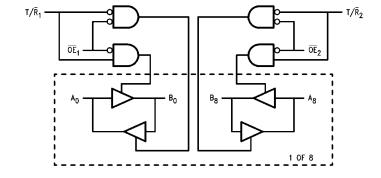
Pin Names	Description				
ŌĒn	Output Enable Input				
T/R _n	Transmit/Receive Input				
A ₀ -A ₁₅	A Bus Inputs/3-STATE Outputs				
B ₀ -B ₁₅	B Bus Inputs/3-STATE Outputs				

Truth Table

Inputs				Output Operating Mode			
Byte1 (0:7)		Byte2	(8:15)				
OE ₁	T/R ₁	OE ₂	T/R ₂	Byte1 (0:7)	Byte2 (8:15)		
L	L	Н	Х	Bus B Data to A	High Z State		
L	Н	Н	Х	Bus A Data to B	High Z State		
Н	Х	L	L	High Z State	Bus B Data to A		
Н	Х	L	Н	High Z State	Bus A Data to B		
L	L	L	L	Bus B Data to A	Bus B Data to A		
L	Н	L	Н	Bus A Data to B	Bus A Data to B		
н	X	н	X	High Z State	High Z State		

H = HIGH Voltage Level L = LOW Voltage Level X = Immaterial

Logic Diagram



Absolute Maximum Ratings(Note 1)

Recommended Operating Conditions

-65°C to +150°C Storage Temperature

Ambient Temperature under Bias -55°C to +125°C

Junction Temperature under Bias -55°C to $+150^{\circ}\text{C}$ V_{CC} Pin Potential to Ground Pin -0.5V to +7.0VInput Voltage (Note 2) -0.5V to +7.0VInput Current (Note 2) -30 mA to +5.0 mA

Voltage Applied to Output

in HIGH State (with $V_{CC} = 0V$)

Standard Output 3-STATE Output -0.5V to +5.5V

Current Applied to Output

in LOW State (Max) Twice the Rated I_{OL} (mA) ESD Last Passing Voltage (Min) 4000V

Free Air Ambient Temperature 0°C to +70°C Supply Voltage +4.5V to +5.5V

-0.5V to V_{CC} Note 1: Absolute maximum ratings are values beyond which the device may be damaged or have its useful life impaired. Functional operation under these conditions is not implied.

Note 2: Either voltage limit or current limit is sufficient to protect inputs.

DC Electrical Characteristics

Symbol	Parameter	Min	Тур	Max	Units	V _{CC}	Conditions
V _{IH}	Input HIGH Voltage	2.0			V		Recognized as a HIGH Signal
V _{IL}	Input LOW Voltage			0.8	V		Recognized as a LOW Signal
V _{CD}	Input Clamp			-1.2	V	Min	10 1
	Diode Voltage			-1.2	V	IVIII	I _{IN} = -18 mA
V _{OH}	Output HIGH	2.4	2.8				$I_{OH} = -3 \text{ mA}$
	Voltage	2.0	2.44		V	Min	$I_{OH} = -15 \text{ mA}$
							(A_n, B_n)
V _{OL}	Output LOW		0.45	0.55	V	Min	I _{OL} = 64 mA
	Voltage		0.43	0.55	v	IVIIII	(A_n, B_n)
IH	Input HIGH Current			5.0	μΑ	Max	$V_{IN} = 2.7V$
I _{BVI}	Input HIGH Current			7.0	μА	Max	$V_{IN} = 7.0V$
	Break-Down Test			7.0	μΛ	IVIAX	$(\overline{OE}_n, T/\overline{R}_n)$
I _{BVIT}	Input HIGH Current			0.1	mA	Max	V _{IN} = 5.5V
	Breakdown Test (I/O)			0.1	IIIA	IVIAX	(A_n, B_n)
I _{IL}	Input LOW			-150	μΑ	Max	$V_{IN} = 0.5V (T/\overline{R}_n, A_n, B_n)$
	Current			-100	μΑ	Max	$V_{IN} = 0.5V (\overline{OE}_n)$
I _{OS}	Output Short-Circuit						V _{OUT} = 0V
00	Current	-100		-225	mA	Max	(A_n, B_n)
I _{IH} +	Output Leakage			05			V _{OUT} = 2.7V
I _{OZH}	Current		0	25	μА	Max	(A_n, B_n)
I _{IL} +	Output Leakage		-20	-150		Max	V _{OUT} = 0.5V
l _{OZL}	Current		-20	-150	μА	iviax	(A_n, B_n)
I _{CEX}	Output HIGH Leakage			50	μА	Max	$V_{OUT} = V_{CC}$
	Current			30	μА	IVIAX	(A_n, B_n)
V _{ID}	Input Leakage	4.75			V	0.0	$I_{ID} = 1.9 \mu A$
	Test	4.73			v	0.0	All Other Pins Grounded
I _{OD}	Output Circuit			3.75	μА	0.0	V _{IOD} = 150 mV
	Leakage Current			5.75	μΑ	0.0	All Other Pins Grounded
I _{ZZ}	Bus Drainage			100	μА	0.0	V _{OUT} = 5.25V
	Test			100	μΛ	0.0	(A_n, B_n)
I _{CCH}	Power Supply Current		70	105	mA	Max	V _O = HIGH
I _{CCL}	Power Supply Current		127	165	mA	Max	$V_0 = LOW$
I _{CCZ}	Power Supply Current		71	105	mA	Max	$V_O = HIGH Z$
C _{IN}	Input Capacitance		8.0		pF	5.0	OE, T/R
			17.0		pF	5.0	A _n , B _n

AC Electrical Characteristics

Symbol	Parameter		$T_A = +25^{\circ}C$ $V_{CC} = +5.0V$ $C_L = 50 \text{ pF}$			$T_A = 0^{\circ}C \text{ to } +70^{\circ}C$ $V_{CC} = +5.0V$ $C_L = 50 \text{ pF}$	
		Min	Тур	Max	Min	Max	
t _{PLH}	Propagation Delay	1.3	2.7	4.3	1.3	4.3	no
t_{PHL}	A_n to B_n or B_n to A_n	1.3	2.2	4.3	1.3	4.3	ns
t _{PZH}	Output Enable Time	3.9	6.9	13.9	3.9	13.9	ns
t_{PZL}		3.9	9.7	13.9	3.9	13.9	115
t _{PHZ}	Output Disable Time	1.8	3.9	6.3	1.8	6.3	ns
t_{PLZ}		1.8	4.4	6.3	1.8	6.3	115

Extended AC Characteristics

Symbol	Parameter	$T_A = 0^{\circ}C$ to $+70^{\circ}C$ $V_{CC} = +5.0V$ $C_L = 50$ pF 16 Outputs Switching (Note 4)		$T_A = 0$ °C to +70°C $V_{CC} = +5.0V$ $C_L = 250 \text{ pF}$ (Note 5)		Unit
		Min	Max	Min	Max	
t _{PLH}	Propagation Delay	1.3	5.8	3.2	8.2	ns
t _{PHL}	A_n to B_n or B_n to A_n	1.3	5.8	3.2	8.2	113
t _{PZH}	Output Enable Time	3.9	14.6			ns
t _{PZL}		3.9	14.6			115
t _{PHZ}	Output Disable Time	1.8	6.3			
t _{PLZ}		1.8	6.3			ns
toshl	Pin-to-Pin Skew		1.2			ns
(Note 3)	for HL Transitions		1.2			115
toslh	Pin-to-Pin Skew		2.2			ns
(Note 3)	for LH Transitions		2.2			115
t _{OST}	Pin-to-Pin Skew		2.5			ns
(Note 3)	for HL/LH Transitions		2.0			

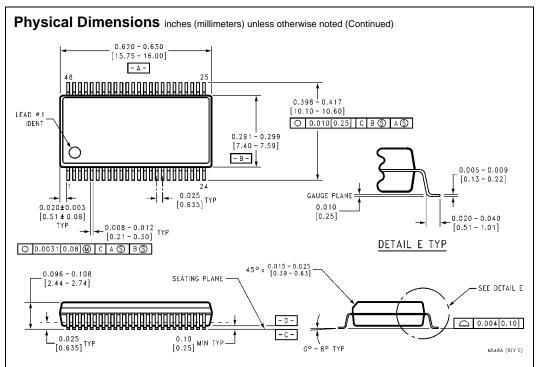
Note 3: Skew is defined as the absolute value of the difference between the actual propagation delays for any two outputs of the same device. The specification applies to any outputs switching HIGH-to-LOW (toosh) LOW-to-HIGH (toosh), or HIGH-to-LOW and/or LOW-to-HIGH (toosh). Specifications guaranteed with all outputs switching in phase.

Note 4: This specification is guaranteed but not tested The limits apply to propagation delays for all paths described switching in phase, i.e., all LOW-to-HIGH, HIGH-to-LOW, 3-STATE-to-HIGH, etc.

Note 5: These specifications guaranteed but not tested. The limits represent propagation delays with 250 pF load capacitors in place of the 50 pF load capacitors in the standard AC load. This specification pertains to single output switching only.

Physical Dimensions inches (millimeters) unless otherwise noted 0.650 +0.006 0.650 -0.000 _ +0.15 _ 16.51 0 _ 0.017±0.004 [0.43±0.10] TYP 45°X 0.045 0.029±0.003 [0.74±0.08] TYP 0.610±0.020 [15.49±0.51] TYP SEATING PLANE 0.020 [0.51] MIN TYP 0.050 [1.27] TYP 0.690-0.005 [17.53-0.13] 0.105±0.015 [2.67±0.38] TYP 0.500 [12.70] TYP 0.165-0.180 [4.19-4.57] TYP □ 0.004[0.10] V44A (REV K)

44-Lead Plastic Lead Chip Carrier (PLCC), JEDEC MO-047, 0.650 Square Package Number V44A



48-Lead Small Shrink Outline Package (SSOP), JEDEC MO-118, 0.300 Wide Package Number MS48A

Fairchild does not assume any responsibility for use of any circuitry described, no circuit patent licenses are implied and Fairchild reserves the right at any time without notice to change said circuitry and specifications.

LIFE SUPPORT POLICY

FAIRCHILD'S PRODUCTS ARE NOT AUTHORIZED FOR USE AS CRITICAL COMPONENTS IN LIFE SUPPORT DEVICES OR SYSTEMS WITHOUT THE EXPRESS WRITTEN APPROVAL OF THE PRESIDENT OF FAIRCHILD SEMICONDUCTOR CORPORATION. As used herein:

- Life support devices or systems are devices or systems which, (a) are intended for surgical implant into the body, or (b) support or sustain life, and (c) whose failure to perform when properly used in accordance with instructions for use provided in the labeling, can be reasonably expected to result in a significant injury to the user.
- A critical component in any component of a life support device or system whose failure to perform can be reasonably expected to cause the failure of the life support device or system, or to affect its safety or effectiveness.

www.fairchildsemi.com